

09/986,096
2000P342686

Please replace the paragraph beginning on page 4, line 12, with the following:

B² An object of the present invention, accordingly, is to provide an SAW filter device, which has a structure capable of preventing destruction of the interdigital transducers by charge generated on the chip substrate due to polarization in such case as when mounting the SAW filter on substrate or when testing the same.

Please replace the paragraph beginning on page 6, line 4, with the following:

B³ SAW filter device according to a preferable embodiment has a SAW filter having the electric discharge preventing means formed on the chip substrate and accommodated in the above package. Since the bottom surface of the chip substrate is in contact with the metal plate portion, charge generated due to polarization thus is not concentrated on the side of the SAW filter chip substrate surface but is neutralized.

Please replace the paragraph beginning on page 9, line 7, with the following:

B⁴ The high resistivity thin film 2 is formed by deposition or sputtering on the chip substrate 1. The interdigital transducer material is formed by, for instance, sputtering Al. Then, a photo-resist is coated, and patterned by an exposure device or the like. After the photo-resist on unnecessary portions is removed, the interdigital transducers 11 to 14 are formed. Alternatively, after forming the high resistivity thin film 2 on the chip substrate 1, a predetermined photo-resist may be provided, and then the interdigital transducer material, such as Al may be formed. The SAW filter as shown in Fig. 1 can be obtained by the above described process.

09/986,096
2000P342686

Please replace the paragraph beginning on page 11, line 12, with the following:

B⁵
As an example, after the formation of the interdigital transducers 11 to 14 on the chip substrate 1 by a sputtering technique or a photo-lithographic technique, the high resistivity thin film 2 is formed by deposition or sputtering on the front surface of the chip substrate 1. As an alternative, it is possible to form the interdigital transducers 11 to 14 on the chip substrate 1 after the formation of the high resistivity thin film 2.

Please replace the paragraph beginning on page 15, line 10, with the following:

B⁶
Fig. 5 (A) is a plan view showing a fifth embodiment of the SAW filter according to the present invention. Fig. 5(B) is a sectional view taken along line B-B. The fifth embodiment of the SAW filter, which has the interdigital patterns 11 to 14 formed on the chip substrate 1 of a piezoelectric material, also has a film 3 of a metal or like conductive material covering an edge portion of the front surface of the chip substrate 1. The conductive material from 3 does not cover the portion constituting a surface wave propagation path in the SAW filter.

Please replace the paragraph beginning on page 18, line 11, with the following:

B⁷
Patterns as second patterns 52 having the same line width as the first pattern 51, are formed such that each forms a gap 53 formed between it and the first pattern 51. Dummy electrode patterns 5 are formed such that they are each connected to each pattern ⁵²5. The gaps 53 have a width (i.e., the spacing between the patterns 51 and 52 is narrower than the spacing between each of the interdigital transducer 12 and 14. The patterns 51 and 52 have a line width narrower than the pattern width of the interdigital transducers 11 to 14.

09/986,096
2000P342686

**Please replace the paragraph beginning on page 21, line 24 and continuing to page 22,
line 2, with the following:**

B⁸
The package 7 has a plurality of pads 71a to 76a formed on a portion 79 defined between the edge wall 77 and the central recess 78. The package 7 further has metal terminals 71 to 76 extending from its inside to the outside. Of the terminals 71 to 76, the terminal 74 is used as a grounding terminal (GND terminal). The pads 71a to 76a are formed such that they are integral with the corresponding terminals 71 to 76.
